

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of:

Examiner: Not yet assigned

Youngyul KIM

Serial No.: 10/506,558

Art Unit: Not yet assigned

Filed: September 1, 2004

Title: ELECTRODE FOR DRY ETCHING A WAFER

Mail Stop AMENDMENT  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

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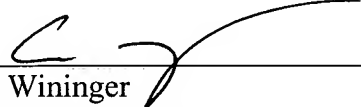
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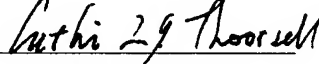
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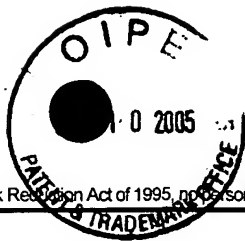
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STATEMENT BY APPLICANT**

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Sheet 1 of 1

**Complete if Known**

Application Number	10/506,558
Filing Date	September 1, 2004
First Named Inventor	Youngyul KIM
Art Unit	Not yet assigned.
Examiner Name	Not yet assigned.
Attorney Docket Number	61282.00015

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	1.	CHO, Byeong-Ok. <i>et al.</i> , "Angular dependence of the redeposition rates during SiO <sub>2</sub> etching in a CF <sub>4</sub> plasma" J. Vac. Sci. Technol. A 19(3) May/Jun 2001, pp. 730-735.	
	2.	LEE, Gyeo-Re <i>et al.</i> "Sidewall-angle effect on the bottom etch profile in SiO <sub>2</sub> etching using a CF <sub>4</sub> Plasma" J. Vac. Sci. Technol. B 19(1), Jan/Feb 2001, pp. 172-178.	
	3.	MIN, Jae-Ho, <i>et al.</i> "Reseposition of Etch Products on Sidewalls During SiO <sub>2</sub> Etching in a Fluorocarbon Plasma. III. Effects of O <sub>2</sub> Addition to CF <sub>4</sub> Plasma" J. Vac. Sci. Technol. B21(4) Jul/Aug 2003 American Vacuum Society, pp. 1210-1215.	
	4.	PINTA, R. <i>et al.</i> "Reactive Etching in SF <sub>6</sub> Gs Mixtures" InP Misfet Technology Vol. 134, No. 1 January 1987, pp. 165-175.	
	5.	ZAROWIN, C.B. "Plasma Etch Anisotropy - Theory and Some Verifying Experiments Relating Ion Transport, Ion Energy, and Etch Profiles" J. Electrochem. Soc.: Solid state Science and Technology, May, 1983, pp. 1144-1152.	

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